

applying a potential so as to deposit a planar film of said conductive material out of the electrolyte solution and over said surface of said patterned substrate,

removing said conductive material from field regions of said patterned substrate while leaving deposits of said conductive material in features defined in said patterned substrate, and

electrically isolating said deposits of said conductive material.

D1 18. (Amended) The layer structure of claim 17, wherein the steps of providing, supplying, applying and removing are performed in the same apparatus.

19. (Amended) The layer structure of claim 18, wherein at least one additional operation of depositing conductive material has been performed after removing said conductive material and before electrically isolating said deposits.

D2 21. (Amended) The layer structure of claim 17, wherein said patterned substrate includes an insulator layer and a barrier layer overlying said insulator layer, wherein said field regions are defined on said insulator layer, and wherein said deposits of said conductive material have been electrically isolated by removal of said barrier layer from said field regions.

58. (Amended) A conductive material structure usable in manufacturing an integrated circuit made by a process comprising:

D3 providing a substrate, wherein the surface of the substrate includes a top portion and cavity portions;

supplying an electrolyte solution out of which a conductive material can be plated, under an applied potential, over the surface of the substrate;

applying a potential so as to deposit a planar film of said conductive material out of the electrolyte solution and on the surface of the substrate; and removing the conductive material from the top portion of the substrate while leaving deposits of the conductive material in the cavities.

D3
59. (Amended) The conductive material of claim 91, wherein at least one additional operation of depositing conductive material has been performed after removing the conductive material.

Please add the following new claims:

--88. The layer structure of claim 18, wherein the step of removing is an electroetching step.

89. The layer structure of claim 18, wherein the step of electrically isolating is carried out using a chemical mechanical polishing process.

D4
90. The layer structure of claim 18, wherein the step of electrically isolating is carried out using a reactive ion etching process.

91. The conductive material structure of claim 58, wherein the steps of providing, supplying, applying and removing are performed in the same apparatus.

92. The conductive material structure of claim 58, wherein the step of removing is an electroetching step.--